

IN THE CLAIMS

Please enter the following pending claims:

54. (Previously Amended) A polish pad comprising:

- a pad center area, said pad center area corresponding to a wafer center area;
- a first set of grooves disposed in said pad center area, said first set of grooves having a first depth;
- a pad edge area disposed adjacent to said pad center area, said pad edge area corresponding to a wafer edge area; and
- a second set of grooves disposed in said pad edge area, said second set of grooves having a second depth.

55. (Previously Added) The polish pad of claim 54 wherein said first depth is smaller than said second depth.

56. (Previously Added) The polish pad of claim 54 wherein said first depth is within the range of approximately 1-90 % of said pad thickness.

57. (Previously Added) The polish pad of claim 54 wherein said second depth is within the range of approximately 1-90 % of said pad thickness.

58. (Previously Added) The polish pad of claim 54 wherein said first set of grooves and said second set of grooves differ in shape.

59. (Previously Amended) A polish pad comprising:

a pad center area, said pad center area corresponding to a wafer center area;
a first set of grooves disposed in said pad center area, said first set of grooves having a first width;

a pad edge area disposed adjacent to said pad center area, said pad edge area corresponding to a wafer edge area; and

a second set of grooves disposed in said pad edge area, said second set of grooves having a second width.

E1 60. (Previously Added) The polish pad of claim 59 wherein said first width is smaller than said second width.

61. (Previously Added) The polish pad of claim 59 wherein said first width is within a range of approximately 1-100 mils.

62. (Previously Added) The polish pad of claim 59 wherein said second width is within the range of approximately 1-100 mils.

63. (Previously Added) The polish pad of claim 59 wherein said first set of grooves and said second set of grooves differ in shape.

64. (Previously Amended) A polish pad comprising:

a pad center area, said pad center area corresponding to a wafer center area;

a first set of grooves disposed in said pad center area, said first set of grooves having a first density;

a pad edge area disposed adjacent to said pad center area, said pad edge area corresponding to a wafer edge area; and

a second set of grooves disposed in said pad edge area, said second set of grooves having a second density.

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65. (Previously Added) The polish pad of claim 64 wherein said first density is smaller than said second density.

66. (Previously Added) The polish pad of claim 64 wherein said first density is within a range of approximately 2-50 grooves/inch.

67. (Previously Added) The polish pad of claim 64 wherein said second density is within a range of approximately 2-50 grooves/inch.

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